

# RJP6085DPK

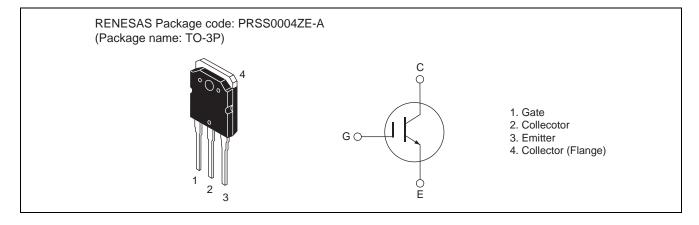
# Silicon N Channel IGBT High Speed Power Switching

REJ03G1862-0100 Rev.1.00 Nov 09, 2009

#### **Features**

- High speed switching
- Low collector to emitter saturation voltage

## **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Collector to Emitter voltage	V <sub>CES</sub>	600	V
Gate to Emitter voltage	V <sub>GES</sub>	±30	V
Collector current	Ic	40	А
Collector peak current	I <sub>C(peak)</sub> Note1	80	А
Collector dissipation	P <sub>C</sub> Note2	178.5	W
Junction to case thermal impedance	θj-c Note2	0.7	°C/W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Pulse width limited by safe operating area.

2. Value at Tc = 25°C

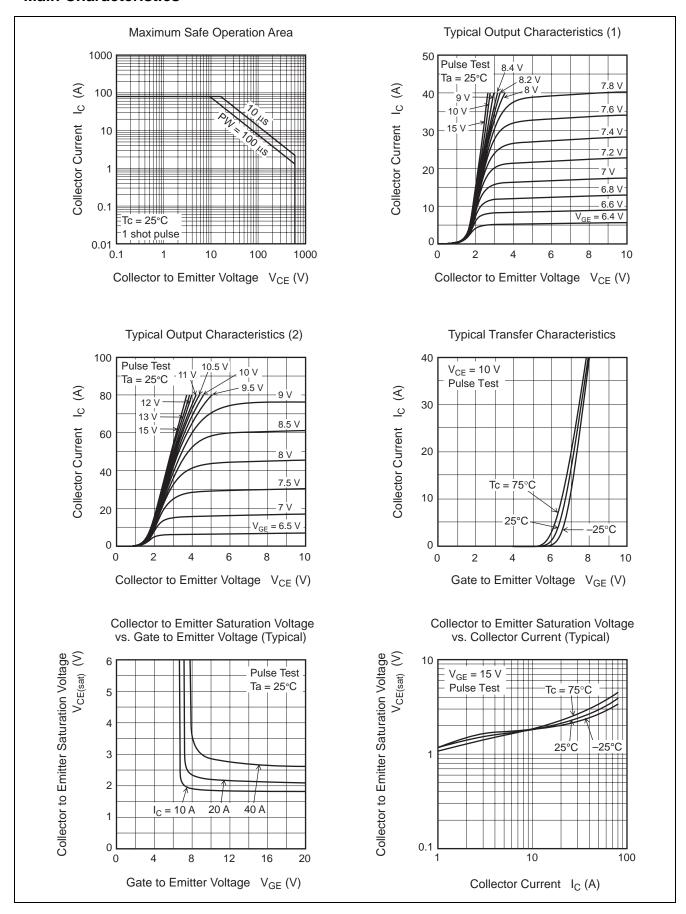
# **Electrical Characteristics**

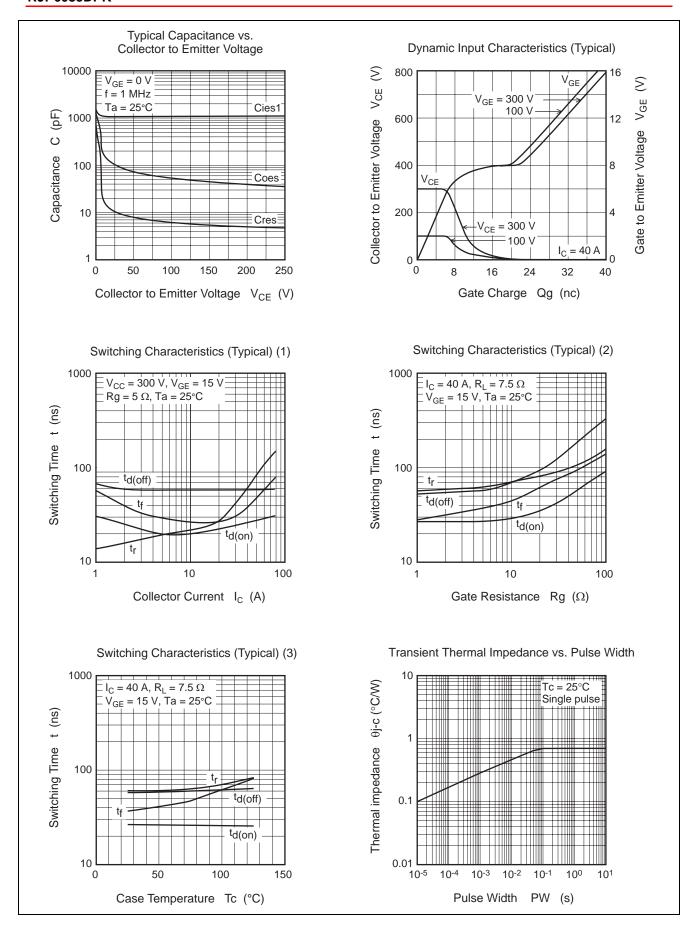
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current	I <sub>CES</sub>		_	10	μΑ	$V_{CE} = 600V, V_{GE} = 0 V$
Gate to emitter leak current	I <sub>GES</sub>		_	±1	μΑ	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0 \text{ V}$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4	_	6	<b>V</b>	$V_{CE} = 10V$ , $I_C = 1$ mA
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>		2.65	3.5	<b>V</b>	$I_C = 40 \text{ A}, V_{GE} = 15 V^{\text{Note3}}$
Input capacitance	Cies		1150	_	pF	V <sub>CE</sub> = 25V
Output capacitance	Coes	_	105	_	pF	$V_{GE} = 0 V$
Reveres transfer capacitance	Cres		12	_	pF	f = 1MHz
Switching time	t <sub>d(on)</sub>		30	_	ns	I <sub>C</sub> = 40 A, Resistive Load
	t <sub>r</sub>		60	_	ns	V <sub>CC</sub> = 300V
	t <sub>d(off)</sub>	_	60	_	ns	$V_{GE} = 15V$
	t <sub>f</sub>	_	40	_	ns	$Rg = 5 \Omega$

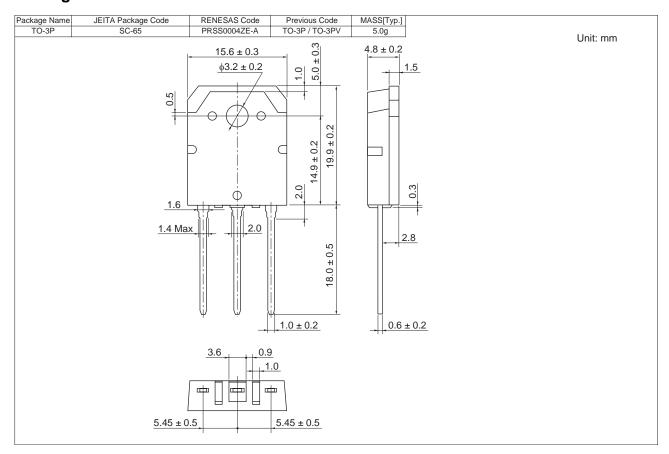
Notes: 3. Pulse test

### **Main Characteristics**





# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK6085DPK-00-T0	360 pcs	Box (Tube)

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

  1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is a subject to change without any plan protein procedure is a subject to change without any plan protein procedure is an advantage of the procedure is a subject of the procedure is an advantage of the procedure is a subject of the procedure is a



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

#### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510